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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/634,667	08/05/2003	Katherina Babich	YOR920030174US1	7152	
75	7590 02/06/2006			EXAMINER	
Ryan, Mason & Lewis, LLP			WALKE, AMANDA C		
Suite 205		•	<u> </u>		
1300 Post Road			ART UNIT	PAPER NUMBER	
Fairfield, CT 06824			1752		
				DATE MALE DAY OF TOOLS	

DATE MAILED: 02/06/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)			
Office Action Summary	10/634,667	BABICH ET AL.			
Onice Action Summary	Examiner	Art Unit			
	Amanda C. Walke	1752			
The MAILING DATE of this communic Period for Reply	ation appears on the cover sheet w	ith the correspondence address			
A SHORTENED STATUTORY PERIOD FO WHICHEVER IS LONGER, FROM THE MA - Extensions of time may be available under the provisions o after SIX (6) MONTHS from the mailing date of this commu - If NO period for reply is specified above, the maximum state - Failure to reply within the set or extended period for reply w Any reply received by the Office later than three months aft earned patent term adjustment. See 37 CFR 1.704(b).	ALING DATE OF THIS COMMUNION of 37 CFR 1.136(a). In no event, however, may a redication.  Utory period will apply and will expire SIX (6) MON it ill, by statute, cause the application to become AE	CATION.  reply be timely filed  ITHS from the mailing date of this communication.  BANDONED (35 U.S.C. § 133).			
Status					
1)⊠ Responsive to communication(s) filed	on 25 November 2005.				
	b)⊠ This action is non-final.				
· <u>—</u>	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is				
•	closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.				
Disposition of Claims					
•	unlication				
	Claim(s) <u>1-31</u> is/are pending in the application.  4a) Of the above claim(s) is/are withdrawn from consideration.				
5) Claim(s) is/are allowed.	e withdrawn from consideration.	•			
6) Claim(s) is/are rejected.					
7) Claim(s) is/are rejected.					
8) Claim(s) are subject to restricti	on and/or election requirement				
Application Papers		-			
9) The specification is objected to by the					
	a) ☐ accepted or b) ☐ objected to				
Applicant may not request that any object		•			
Replacement drawing sheet(s) including t					
11)☐ The oath or declaration is objected to	by the Examiner. Note the attached	d Office Action or form PTO-152.			
Priority under 35 U.S.C. § 119					
12) Acknowledgment is made of a claim for	or foreign priority under 35 U.S.C.	§ 119(a)-(d) or (f).			
a) ☐ All b) ☐ Some * c) ☐ None of:		,			
1. Certified copies of the priority d	ocuments have been received.	·			
2. Certified copies of the priority d		pplication No			
3. Copies of the certified copies o	f the priority documents have been	received in this National Stage			
application from the Internation	al Bureau (PCT Rule 17.2(a)).				
* See the attached detailed Office action	for a list of the certified copies not	received.			
Attachment(s)					
1) Notice of References Cited (PTO-892)		Summary (PTO-413)			
2) Notice of Draftsperson's Patent Drawing Review (PT	The second secon	s)/Mail Date nformal Patent Application (PTO-152)			
<ol> <li>Information Disclosure Statement(s) (PTO-1449 or P Paper No(s)/Mail Date</li> </ol>	(TO/SB/08) 3) ☐ Notice of 1				
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## **DETAILED ACTION**

In light of Applicant's arguments, the rejection made in the previous office action has been dropped and a new rejection follows.

## Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-31 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kennedy et al (6,506, 497) in view of Bening (2005/0107541) and Feder et al (6,521,699).

Kennedy et al disclose anti-reflective coating materials for deep ultraviolet photolithography include one or more organic light-absorbing compounds incorporated into spin-on-glass materials. Suitable absorbing compounds are strongly absorbing over wavelength ranges around wavelengths such as 365 nm, 248 nm, and 193 nm that may be used in photolithography. A method of making absorbing spin-on-glass materials includes combining one or more organic absorbing compounds with alkoxysilane or halosilane reactants during synthesis of the spin-on-glass materials.

An anti-reflective coating material for deep ultraviolet photolithography includes one or more organic absorbing compounds incorporated into a spin-on-glass (SOG) material. The spin-on-glass materials include methylsiloxane, methylsilsesquioxane, phenylsiloxane, phenylsilsesquioxane, methylphenylsilsesquioxane, and silicate polymers. As used herein, spin-on-glass materials also include hydrogensiloxane polymers of the general

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formula (H<sub>0-1.0</sub> SiO<sub>1.5-2.0</sub>) x and hydrogensilsesquioxane polymers, which have the formula (HsiO 1.5) x, where x is greater than about 8. Also included are copolymers of hydrogensilsesquioxane and alkoxyhydridosiloxane or hydroxyhydridosiloxane. Spin-on-glass materials additionally include organohydridosiloxane polymers of the general formula  $(H_{0-1.0} \text{SiO}_{1.5-2.0})$   $(R_{0-1.0} \text{SiO}_{1.5-2.0})$ 2.0)m, and organohydridosilsesquioxane polymers of the general formula (HsiO<sub>1.5</sub>).sub.n (RSiO<sub>1.5</sub>).sub.m, where m is greater than 0 and the sum of n and m is greater than about 8 and R is alkyl or aryl. Coating solutions of spin-on-glass materials incorporating absorbing comounds are used to form anti-reflecting films on various layers in integrated circuit devices. Absorbing compounds suitable for use with the present invention are strongly absorbing at wavelengths less than about 375 nm or less than about 260 nm. In particular, suitable absorbing compounds are strongly absorbing over at least an approximately 10 nm wide wavelength range around wavelengths such as 248 nm, 193 nm, or other ultraviolet wavelengths, such as 365 nm, that may be used in photolithography. The chromophores of suitable compounds typically have from one to three benzene rings that may or may not be fused. Incorporatable absorbing comounds have an accessible reactive group attached to the chromophore, the reactive groups including hydroxyl groups, amine groups, carboxylic acid groups, and substituted silyl groups with silicon bonded to one, two, or three alkoxy group or halogen atom substituents. The reactive groups may be directly bonded to the chromophore or the reactive groups may be attached to the chromophore through a hydrocarbon bridge.

Examples of suitable organic absorbing compounds include anthraflavic acid, 9-anthracene carboxylic acid, 9-anthracene methanol, alizarin, quinizarin, primuline, 2-hydroxy-4(3-triethoxysilylpropoxy)-diphenylketone, rosolic acid, triethoxysilylpropyl-1,8-naphthalimide,

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9-anthracene carboxy-methyl triethoxysilane, phenyltriethoxysilane, azo compounds, such as 4-phenylazophenol, and mixtures thereof.

The reference teaches that conventional additives may be included in the layer, but fails to specifically mention a cross-linking agent, and while provides examples of silesquioxane compounds, fails to disclose a specific compound meeting the instant claim limitations.

Bening disclose 3D polyhedral oligosilesquioxane polymers that aid in croslinking. The POSS polymers taught by the reference appear to meet the instant claim limitations, as the polymer has the same formula, and n is preferably 8 [0028].

Given the teachings of the references, it would have been obvious to one of ordinary skill in the art to prepare the material of Kennedy et al choosing to employ the silesquioxane polymer to aid cross-linking taught by Bening with reasonable expectation of achieving a material able to form a pattern having small features.

Feder et al disclose a layer similar to that of Kennedy et al. The reference teaches that polysilsesquioxane compositions conventionally comprise cross-linking agents (see abstract).

Given the teachings of the references, it would have been obvious to one of ordinary skill in the art to prepare the material of Kennedy et al in view of Bening choosing to employ a cross-linking agent with reasonable expectation of achieving a material able to form a pattern having small features.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Amanda C. Walke whose telephone number is 571-272-1337. The examiner can normally be reached on M-R 5:30-4.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Cynthia Kelly can be reached on 571-272-1526. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Amanda C Walke

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Examiner

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ACW February 3, 2006